

# OPA6611EU

## Red LED Chip

Super Bright / Eutectic Metal

GaAlAs / GaAs

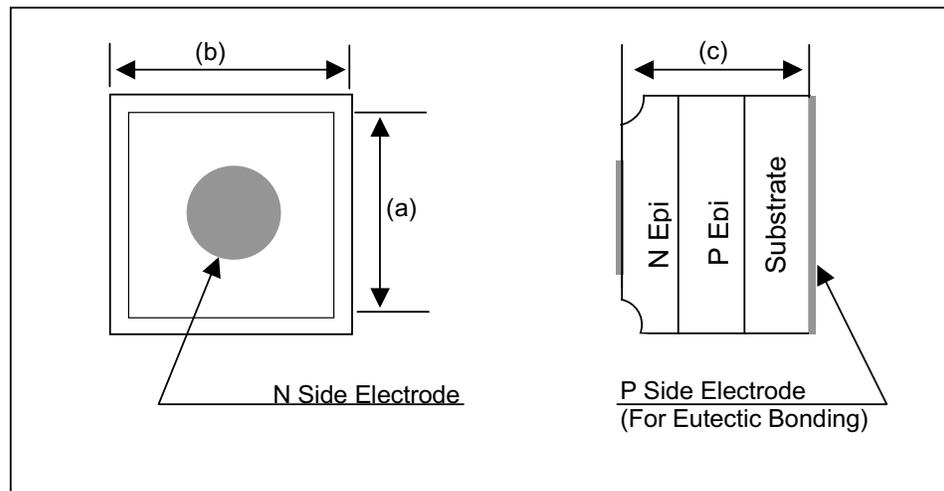
- 1. Material** Substrate GaAs (P Type)  
Epitaxial Layer GaAlAs (N/P Type)
- 2. Electrode** N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy (AuGe Eutectic Metal)

### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1\text{mA}$
	$V_{F(2)}$		1.8	2.2	V	$I_F=20\text{mA}$
Reverse Voltage	$V_R$	5.0			V	$I_R=10\mu\text{A}$
Brightness	$I_V$	400	550		mcd	$I_F=20\text{mA}$
Wavelength	Hue		645		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		20		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1<sup>3</sup>/<sub>4</sub> plastic package.

- 4. Mechanical Data**
- (a) Emission Area ----- 10mil × 10mil
  - (b) Bottom Area ----- 12mil × 12mil
  - (c) Chip Thickness ----- 11mil



Knowledge\*on Inc.

For more information, visit our website at [www.knowledge-on.com](http://www.knowledge-on.com)

513-37 Eoyang-dong, Iksan, 570-210, Korea. Tel: +82-63-839-1111. Fax: +82-63-835-8259

